Part Number	Customer

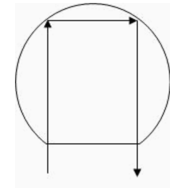
Category		**Parameter**	**Specification**	**Measurement Method**
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	WaferVendor
	2.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	{110}+/- 0.5 degree	Wafer Vendor
	4.0	Secondary Flat Orientation	None	
	5.0	Overall Thickness	400.00 +/- 5.00 um	Wafer Vendor
	6.0	Total Thickness Variation (TTV)	<10.00um	Guaranteed by process
	7.0	Bow	<40.00um	ADE to ASTM F534, 20%
	8.0	Warp	<40.00um	ADE to ASTM F657, 20%
	9.0	Back Surface Quality	Polished with light handling marks and custom lasermarking	Guaranteed by process
	10.0	Front Surface Quality	Prime (Polished)	Guaranteed by process
	11.0	Edge Chips	None	Bright Light 100%
	12.0	Lasermarking	On wafer Backside opposite the flat. Dimensions 14mm x 1.8mm. See attachment	
	13.0	Edge Exclusion	5mm	
HandleSilicon	14.0	Handle Thickness	400.00 +/- 5.00 um	Wafer Vendor
	15.0	Handle Growth Method	CZ	Wafer Vendor
	16.0	Handle Doping Type	P	Wafer Vendor
	17.0	Handle Dopant	Boron	Wafer Vendor
	18.0	Handle Resistivity	1- 10 ohm-cm	Wafer Vendor
	19.0	Handle Orientation	{100}+/- 0.5 degree	Wafer Vendor
	20.0	Surface Haze	None	Bright Light, 100% (note 2).
	21.0	Total scratch length	Frontside - Total <10mm	Bright Light, 100% (note 2).

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

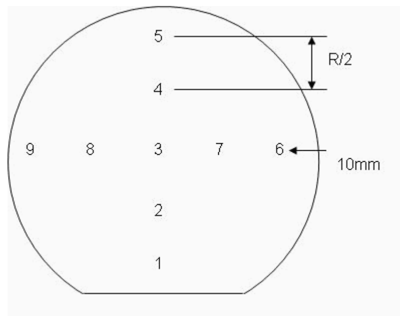
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information